

Silicon PNP Power Transistors

2SB743

DESCRIPTION

With TO-126 package

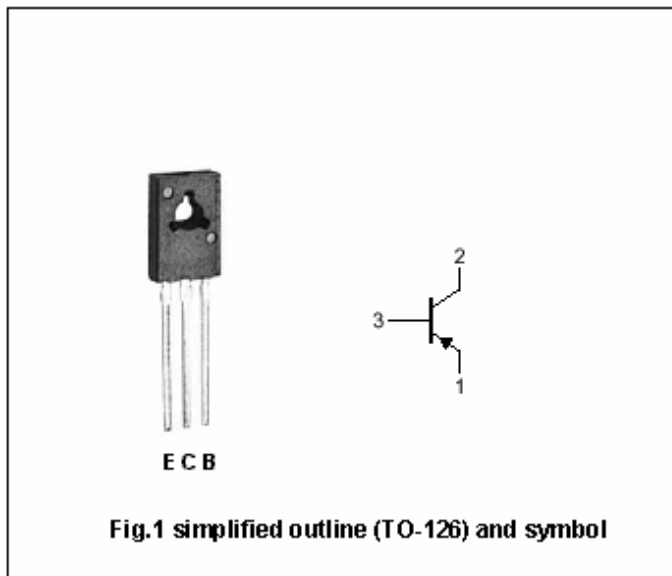
- Low collector saturation voltage
- Excellent h_{FE} linearity

APPLICATIONS

- For audio frequency power amplifier and general purpose applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-40	V
V_{CEO}	Collector-emitter voltage	Open base	-30	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current (DC)		-3	A
I_{CM}	Collector current-Peak		-5	A
I_B	Base current		-0.6	A
P_C	Collector power dissipation	$T_a=25^\circ C$	1.0	W
		$T_C=25^\circ C$	10	
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA; I _B =0	-30			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-0.15A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-1.5A; I _B =-0.15A			-2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-1	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1	μA
h _{FE-1}	DC current gain	I _C =-20mA; V _{CE} =-5V	30			
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-5V	60		320	
f _T	Transition frequency	I _C =-0.1A; V _{CE} =-5V		55		MHz

PACKAGE OUTLINE

